

BC556/BC557/BC558 TRANSISTOR (PNP)

FEATURES

- High Voltage
- Complement to BC546/BC547/BC548

MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

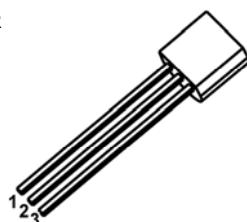
Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage BC556	-80	V
	BC557	-50	
	BC558	-30	
V_{CEO}	Collector-Emitter Voltage	-65	V
		-45	
		-30	
V_{EBO}	Emitter-Base Voltage	-5	V
I_c	Collector Current -Continuous	-100	mA
P_c	Collector Power Dissipation	625	mW
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55-150	$^\circ\text{C}$

TO-92

1. COLLECTOR

2. BASE

3. Emitter

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage BC556 BC557 BC558	V_{CBO}	$I_C = -100\mu\text{A}, I_E = 0$	-80			V
			-50			
			-30			
Collector-emitter breakdown voltage BC556 BC557 BC558	V_{CEO}	$I_C = -2\text{mA}, I_B = 0$	-65			V
			-45			
			-30			
Emitter-base breakdown voltage	V_{EBO}	$I_E = -100\mu\text{A}, I_C = 0$	-5			V
Collector cut-off current BC556 BC557 BC558	I_{CBO}	$V_{CB} = -70\text{ V}, I_E = 0$ $V_{CB} = -45\text{ V}, I_E = 0$ $V_{CB} = -25\text{ V}, I_E = 0$			-0.1	μA
Collector cut-off current BC556 BC557 BC558	I_{CEO}	$V_{CE} = -60\text{ V}, I_B = 0$ $V_{CE} = -40\text{ V}, I_B = 0$ $V_{CE} = -25\text{ V}, I_B = 0$			-0.1	μA
Emitter cut-off current BC556 BC557 BC558	I_{EBO}	$V_{EB} = -5\text{ V}, I_C = 0$			-0.1	μA
DC current gain BC556 BC557 BC558 BC557A BC556B/BC557B/BC558B BC557C	h_{FE}	$V_{CE} = -5\text{V}, I_C = -2\text{mA}$	120		800	
			120		800	
			120		800	
			120		220	
			180		460	
			420		800	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100\text{mA}, I_B = -5\text{mA}$			-0.65	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -100\text{mA}, I_B = -5\text{mA}$			-1	V
Transition frequency	f_T	$V_{CE} = -5\text{V}, I_C = -10\text{mA}$ $f = 100\text{MHz}$	150			MHz